Dual N-Channel 20-V (D-S) MOSFET

Key Features:

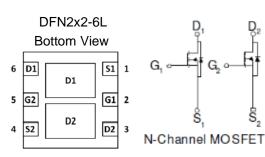
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

Typical	App	lications:
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- Power Routing
- · Li Ion Battery Packs
- · Level Shifting and Driver Circuits

PRODUCT SUMMARY					
V _{DS} (V)	I□ (A)				
20	$23 @ V_{GS} = 4.5V$	6.6			
20	$33 @ V_{GS} = 2.5V$	5.6			





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Symbol	Limit	Units	
Drain-Source Voltage			V_{DS}	20	V	
Sate-Source Voltage				±8	V	
Continuous Dusin Commental		T _A =25°C	ı	6.6		
Continuous Drain Current ^a		T _A =70°C	l _D	5.3	Α	
Pulsed Drain Current ^b				25		
Continuous Source Current (Diode Conduction) a				2.1	Α	
Dower Dissipation a		T _A =25°C	P _D	1.5	W	
Power Dissipation ^a	T _A =70°C			0.95	v v	
Operating Junction and Storage Temperature Range				-55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	50	°C/W			
Maximum Junction-to-Ambient	Steady State	ГХ⊕ЈА	105	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

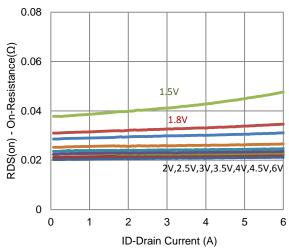
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.4			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	lana	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA		
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α		
Drain Cauras On Basistanas a	r	$V_{GS} = 4.5 \text{ V}, I_D = 5.3 \text{ A}$			23	mΩ		
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 4.3 \text{ A}$			33			
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 5.3 \text{ A}$		5		S		
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 1.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.73		V		
		Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		11		nC		
Gate-Source Charge	Q_{gs}	$I_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 5.3 \text{ A}$		2.1				
Gate-Drain Charge	Q_gd	ID = 3.3 A		2.9				
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 10 \text{ V}, R_{L} = 1.9 \Omega,$		7				
Rise Time	t _r	$V_{DS} = 10 \text{ V}, R_L - 1.9 \Omega,$ $I_D = 5.3 \text{ A},$		31		- ns		
Turn-Off Delay Time	t _{d(off)}	$t_{d(off)}$ $V_{GEN} = 4.5 \text{ V, } R_{GEN} = 6 \Omega$		55				
Fall Time	t _f	V GEN - 4.5 V, T GEN - 0 12		17				
Input Capacitance	C _{iss}			726				
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		74		pF		
Reverse Transfer Capacitance	erse Transfer Capacitance C _{rss}			69				

Notes

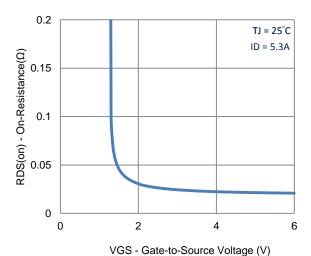
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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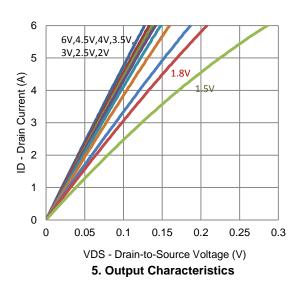
Typical Electrical Characteristics

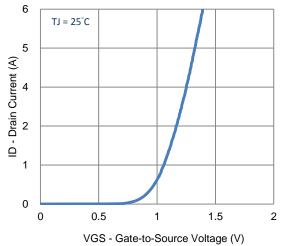


1. On-Resistance vs. Drain Current

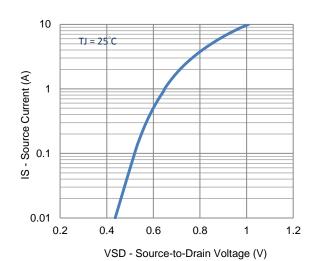


3. On-Resistance vs. Gate-to-Source Voltage

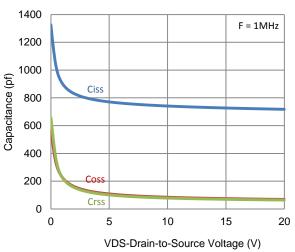




2. Transfer Characteristics

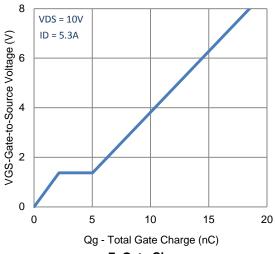


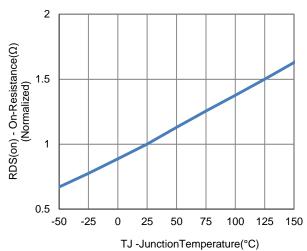
4. Drain-to-Source Forward Voltage



6. Capacitance

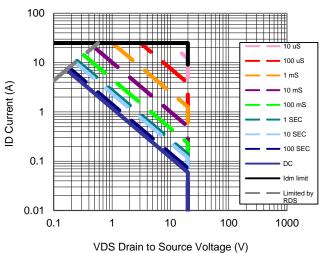
Typical Electrical Characteristics

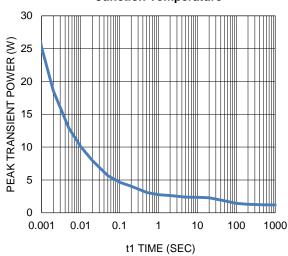




7. Gate Charge

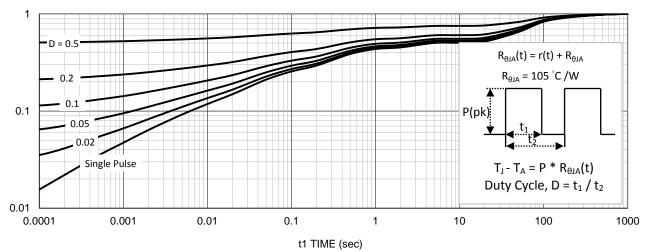






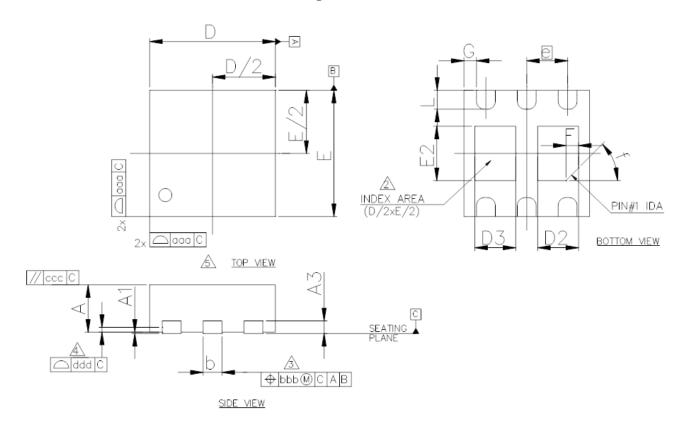
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONS IN MILLIMETERS			П	DIMENSIONS IN INCHES				
	MIN.	NOM.	MAX.	11	MIN.	NOM.	MAX.		
A	0.70	0.75	0.80	П	0.028	0.030	0.032		
A1	0.00	0.02	0.05	П	0.000	0.001	0.002		
A.3		0.20 ref		П		[0.008 ref]			
ь	0.25	0.30	0.35	П	0.010	0.012	0.014		
_ D_	2.00 BSC			П	0.079 BSC				
D2	0.60	0.65	0.70	П	0.024	0.026	0.028		
D3	0.60	0.65	0.70	П	0.024	0.026	0.028		
E	2.00 BSC			П	0.079 BSC				
E2	0.81	0.86	0.91	П	0.032	0.034	0.036		
<u>e</u>	0.05	0.65_BSC	0.75	П		0.026 BSC	0.014		
-	0.25	0.30	0.35	н	0.010	0.012	0.014		
F		0.20 REF		П	0.008 REF				
f		45?		П		45?			
G	0.15	0.20	0.25	П	0.006	0.008	0.010		
000	0.15				0.006				
bbb		0.10		П	0.004				
ccc		0.10		П	0.004				
ddd		0.08		Ц		0.003			